

Dual Serise Switching Diodes

FEATURES

- Ultra high speed switching
- Suitable for high packing density layout.
- High reliability.
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

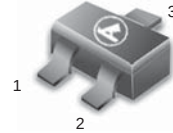
DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LDAN202UT1G S- LDAN202UT1G	N	3000/Tape&Reel
LDAN202UT3G S- LDAN202UT3G	N	10000/Tape&Reel

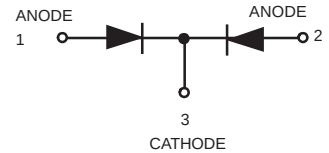
MAXIMUM RATINGS (Each Diode)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Forward Current	I_o	100	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	300	mAdc
Forward voltage($I_f = 100mA$)	V_F	1.2	V
Reverse current($V_r = 70V$)	I_R	0.1	uA
Capacitance between terminals($f = 1MHz$)	C_T	3.5	pF
Reverse recovery time($V_r = 6V, I_f = 5mA$)	T_{rr}	4	nS

LDAN202UT1G
S-LDAN202UT1G



SC-70



ELECTRICAL CHARACTERISTIC CURVES

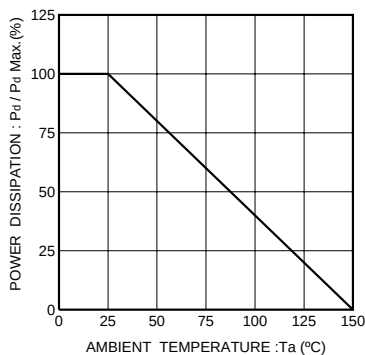


Fig.1 Power attenuation curve

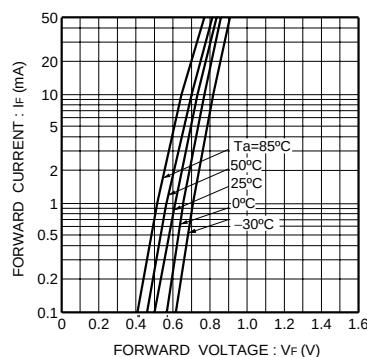


Fig.2 Forward characteristics (P Type)

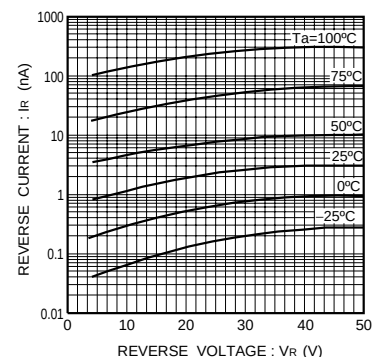


Fig.3 Reverse characteristics (P Type)

LDAN202UT1G, S-LDAN202UT1G

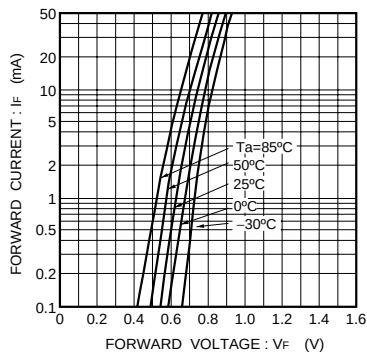


Fig.4 Forward characteristics (N Type)

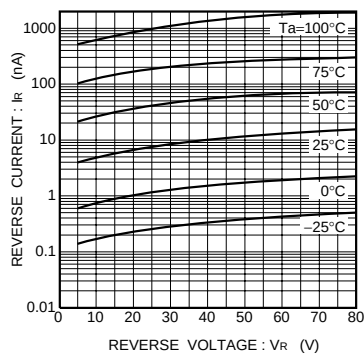


Fig.5 Reverse characteristics (N Type)

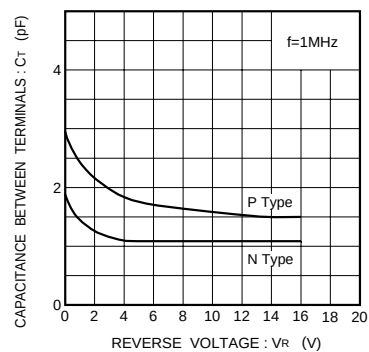


Fig.6 Capacitance between terminals characteristics

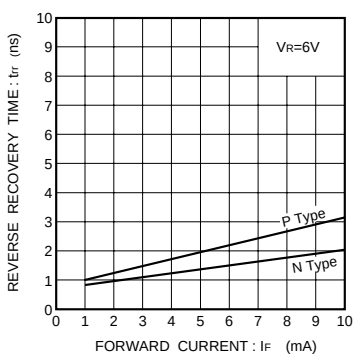


Fig.7 Reverse recovery time

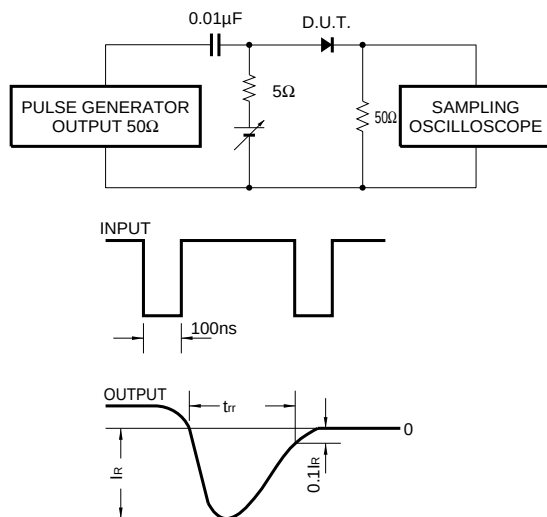


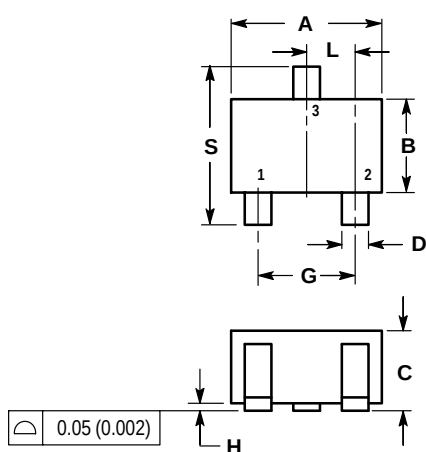
Fig.8 Reverse recovery time (t_{rr}) measurement circuit

LDAN202UT1G, S-LDAN202UT1G

SC-70

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
N	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40

